

IN THE CLAIMS:

Please cancel claims 1-7 and add the following new claims 8-12.

Claims 1-7 (cancelled).

8. (New) A semiconductor device, comprising:
a semiconductor substrate; and
a metal electrode portion provided as a bump protruding from a surface of the substrate, the bump having a planar top surface facing away from the substrate, the bump extending along the surface of the substrate, beyond a periphery of a joint portion between the bump and the semiconductor substrate.
9. (New) A semiconductor device according to claim 8, wherein the bump has a recess extending over an entire peripheral edge of the planar top surface.
10. (New) A transfer substrate for electrode transfer therefrom onto a semiconductor device, comprising:
a substrate;
a seed film on the substrate; and
a patterning film on the substrate, the patterning film partly covering a surface of the seed film so as to expose a metal electrode receiving portion of the seed film.
11. (New) A transfer substrate according to claim 10, further comprising a metal electrode portion provided on the exposed metal electrode portion of the seed film.
12. (New) A transfer substrate according to claim 10, wherein the seed film is composed of such a material that the metal electrode portion has a lower adhesion affinity for the seed film than for a portion of the semiconductor device onto which the metal electrode portion is to be transferred.